



SEMITRANS® 10

IGBT R8 Modules

SKM1000GB17R8

Features*

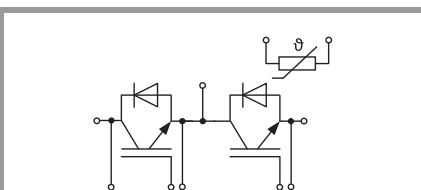
- Symmetrical current sharing
- Low-inductive module design
- High mechanical robustness
- UL recognized, file no. E63532

Typical Applications

- Motor Drives
- UPS Systems
- Solar Inverters

Remarks

Recommended $T_{jop} = -40 \dots +150^\circ\text{C}$



GB

Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1700	V	
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	1574	A
		$T_c = 100^\circ\text{C}$	1027	A
I_{Cnom}		1000	A	
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	2000	A	
V_{GES}		-20 ... 20	V	
t_{psc}	$V_{CC} = 1200\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1700\text{ V}$	$T_j = 150^\circ\text{C}$	10	μs
T_j		-40 ... 175	$^\circ\text{C}$	
Inverse diode				
V_{RRM}	$T_j = 25^\circ\text{C}$	1700	V	
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	1449	A
		$T_c = 100^\circ\text{C}$	905	A
I_{Fnom}		1000	A	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	2000	A	
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	6240	A	
T_j		-40 ... 175	$^\circ\text{C}$	
Module				
T_{stg}		-40 ... 150	$^\circ\text{C}$	
V_{isol}	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V	

Characteristics						
Symbol	Conditions	min.	typ.	max.	Unit	
IGBT						
$V_{CE(sat)}$	$I_C = 1000\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.66	1.99	V	
		$T_j = 150^\circ\text{C}$	2.01	2.33	V	
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	1.06	1.12	V	
		$T_j = 150^\circ\text{C}$	0.95	1.05	V	
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	0.60	0.87	$\text{m}\Omega$	
		$T_j = 150^\circ\text{C}$	1.06	1.28	$\text{m}\Omega$	
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 36\text{ mA}$	5	5.8	6.5	V	
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1700\text{ V}, T_j = 25^\circ\text{C}$			6.0	mA	
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	90.0		nF	
C_{oes}			3.00		nF	
C_{res}			0.24		nF	
Q_G	$V_{GE} = -15\text{ V} / +15\text{ V}$		5640	nC		
R_{Gint}	$T_j = 25^\circ\text{C}$		1.8	Ω		
$t_{d(on)}$	$V_{CC} = 900\text{ V}$	$T_j = 150^\circ\text{C}$	476		ns	
t_r	$I_C = 1000\text{ A}$ $V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	105		ns	
		$T_j = 150^\circ\text{C}$	465		mJ	
E_{on}	$R_{Gon} = 0.7\ \Omega$	$T_j = 150^\circ\text{C}$	713		ns	
$t_{d(off)}$	$R_{Goff} = 0.7\ \Omega$	$T_j = 150^\circ\text{C}$	158		ns	
t_f	$di/dt_{on} = 7.8\text{ kA}/\mu\text{s}$ $di/dt_{off} = 4.8\text{ kA}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	332		mJ	
			$dv/dt = 4600\text{ V}/\mu\text{s}$ $L_s = 24\text{ nH}$			
E_{off}		$T_j = 150^\circ\text{C}$	0.03		K/W	
$R_{th(j-c)}$	per IGBT		0.016		K/W	
$R_{th(c-s)}$	per IGBT ($\lambda_{grease} = 0.81\text{ W}/(\text{m}^2\text{K})$)				K/W	

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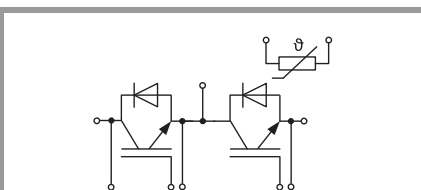
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 1000 \text{ A}$ $V_{GE} = 0 \text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$		1.78	2.12	V
		$T_j = 150^\circ\text{C}$		1.81	2.14	V
V_{F0}	chipelevel	$T_j = 25^\circ\text{C}$		1.32	1.56	V
		$T_j = 150^\circ\text{C}$		1.08	1.22	V
r_F	chipelevel	$T_j = 25^\circ\text{C}$		0.46	0.56	m Ω
		$T_j = 150^\circ\text{C}$		0.73	0.92	m Ω
I_{RRM}	$I_F = 1000 \text{ A}$	$T_j = 150^\circ\text{C}$		711		A
Q_{rr}	$di/dt_{off} = 8.1 \text{ kA}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		325		μC
E_{rr}	$V_{GE} = -15 \text{ V}$ $V_{CC} = 900 \text{ V}$	$T_j = 150^\circ\text{C}$		159		mJ
$R_{th(j-c)}$	per diode				0.042	K/W
$R_{th(c-s)}$	per diode ($\lambda_{grease}=0.81 \text{ W}/(\text{m}^2\text{K})$)			0.017		K/W
Module						
L_{CE}				10		nH
$R_{CC'+EE'}$	measured per switch, $T_C = 25^\circ\text{C}$			0.2		m Ω
$R_{th(c-s)1}$	calculated without thermal coupling ($\lambda_{grease}=0.81 \text{ W}/(\text{m}^2\text{K})$)			0.0041		K/W
$R_{th(c-s)2}$	including thermal coupling, T_s underneath module ($\lambda_{grease}=0.81 \text{ W}/(\text{m}^2\text{K})$)			0.007		K/W
M_s	to heat sink M5		4		6	Nm
M_t	to terminals M8		8		10	Nm
	to terminals M4		1.8		2.1	Nm
w					1250	g
Temperature Sensor						
R_{100}	$T_c=100^\circ\text{C}$ ($R_{25}=5 \text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R(T)=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; $T[\text{K}]$;			3550 $\pm 2\%$		K

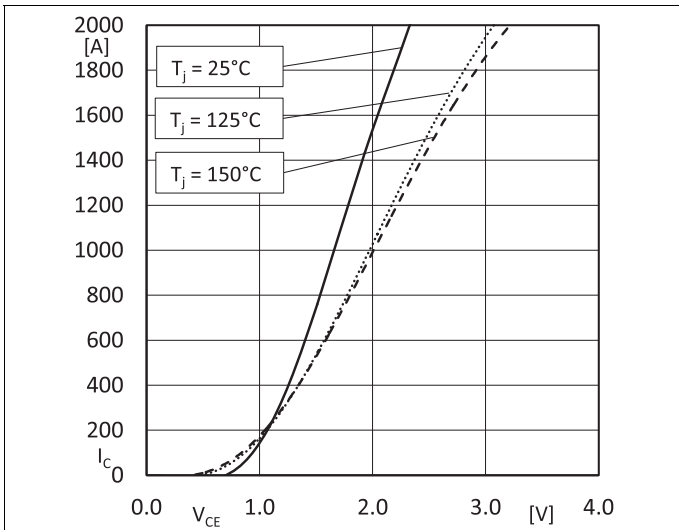


Fig. 1: Output characteristics IGBT (typical); $I_C = f(V_{CE})$; $V_{GE} = 15V$; (chipelevel)

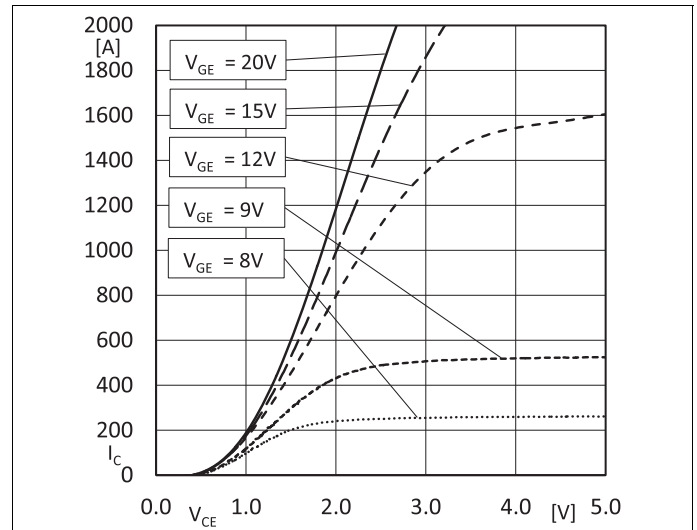


Fig. 2: Output characteristics IGBT (typical); $I_C = f(V_{CE})$; $T_j = 150^\circ C$; (chipelevel)

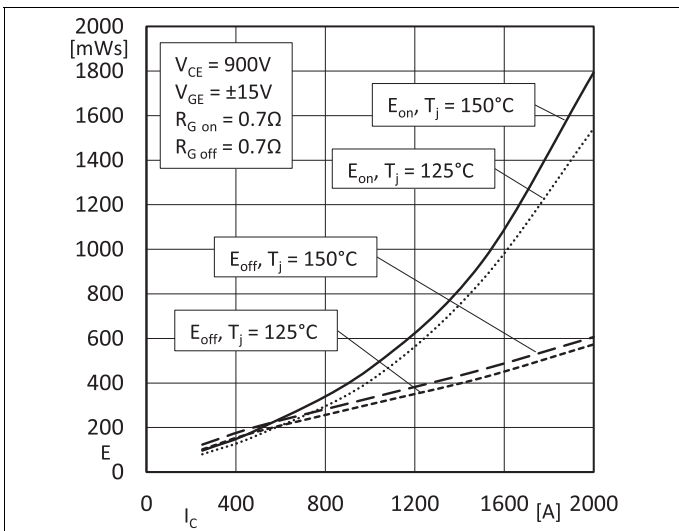


Fig. 3: Switching losses IGBT (typical); $E=f(I_C)$

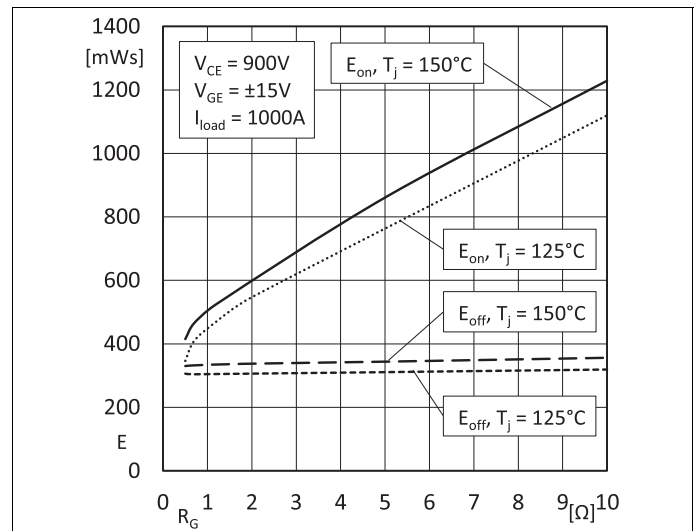


Fig. 4: Switching losses IGBT (typical); $E=f(R_G)$

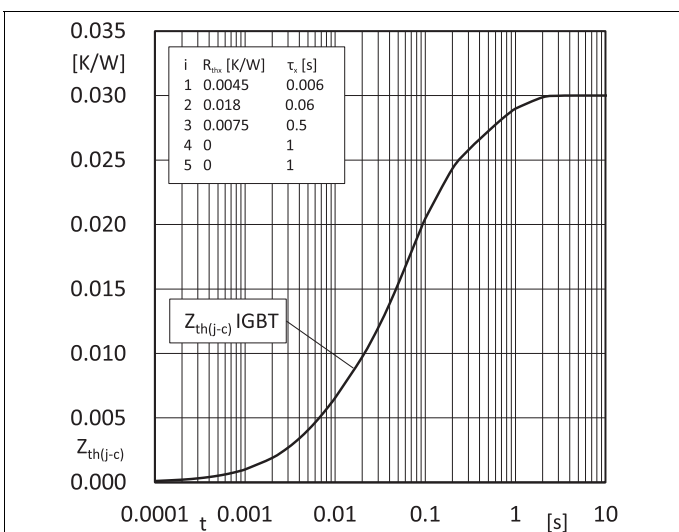


Fig. 5: Transient thermal impedance IGBT

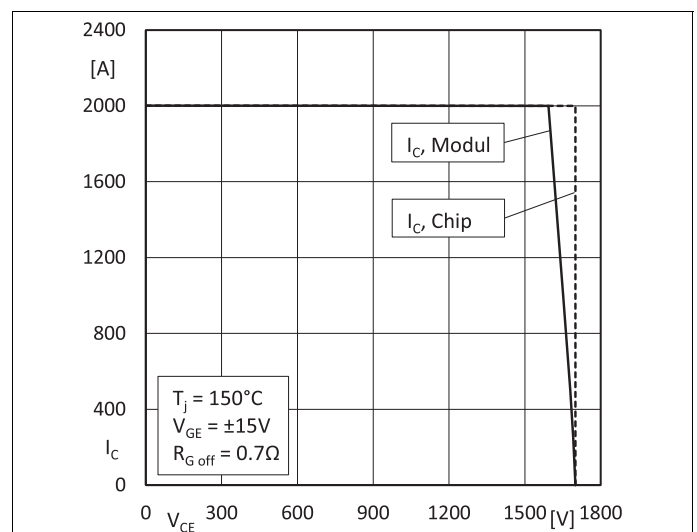


Fig. 6: RBSOA IGBT

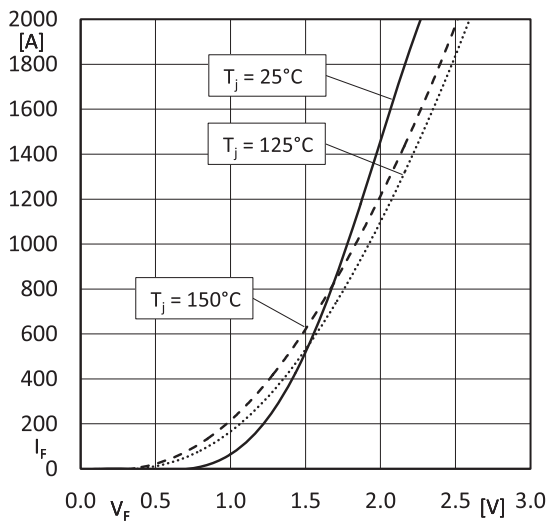


Fig. 7: Forward charact. Diode (typical); $I_F = f(V_F)$; (chipllevel)

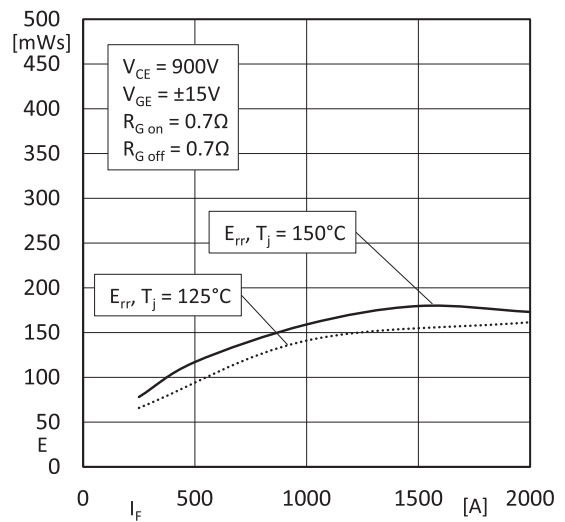


Fig. 8: Switching losses Diode (typical); $E = f(I_F)$

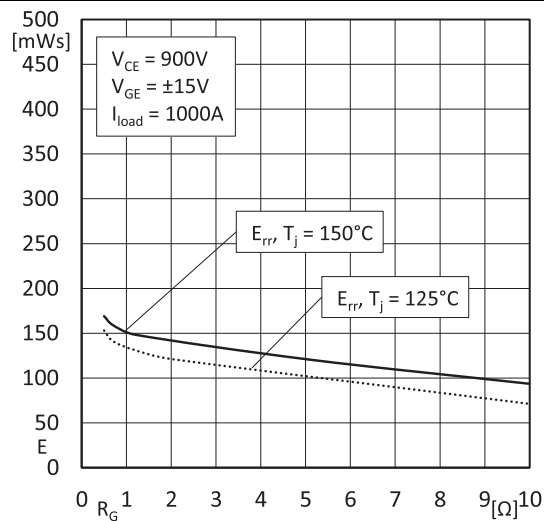


Fig. 9: Switching losses Diode (typical); $E = f(R_G)$

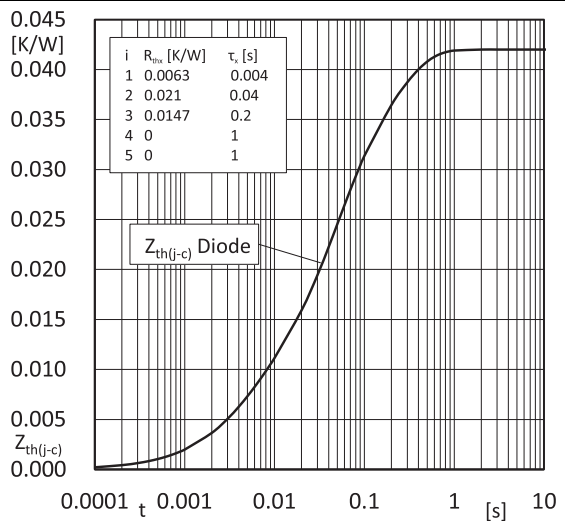


Fig. 10: Transient thermal impedance Diode

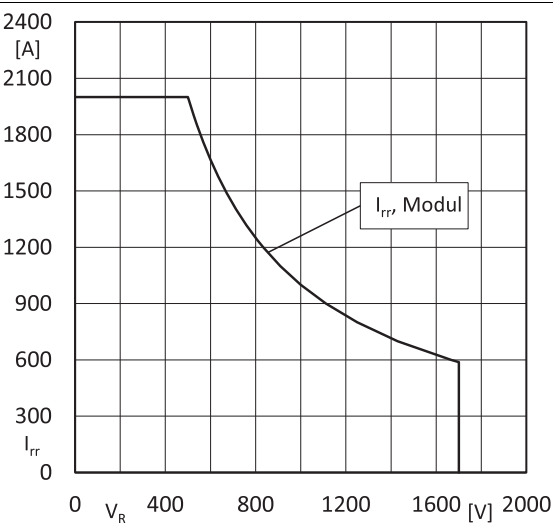


Fig. 11: RBSOA Diode

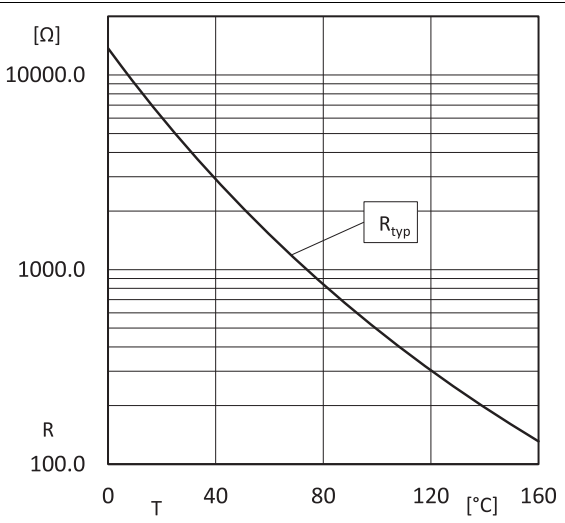


Fig. 12: NTC characteristics (typical)

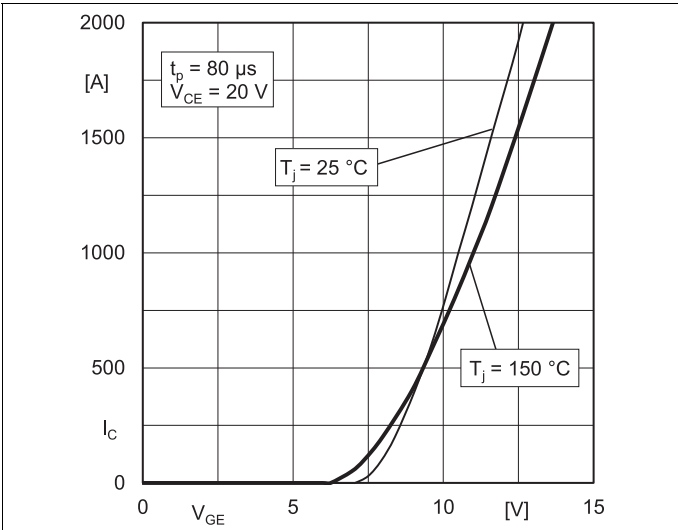


Fig. 13: Typ. transfer characteristic

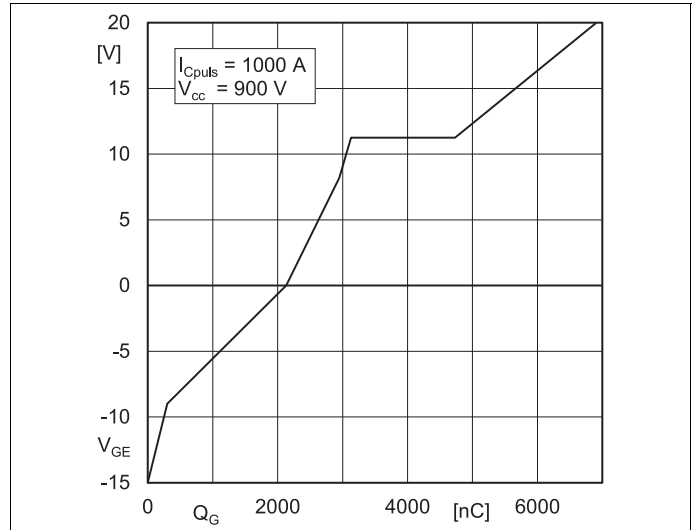
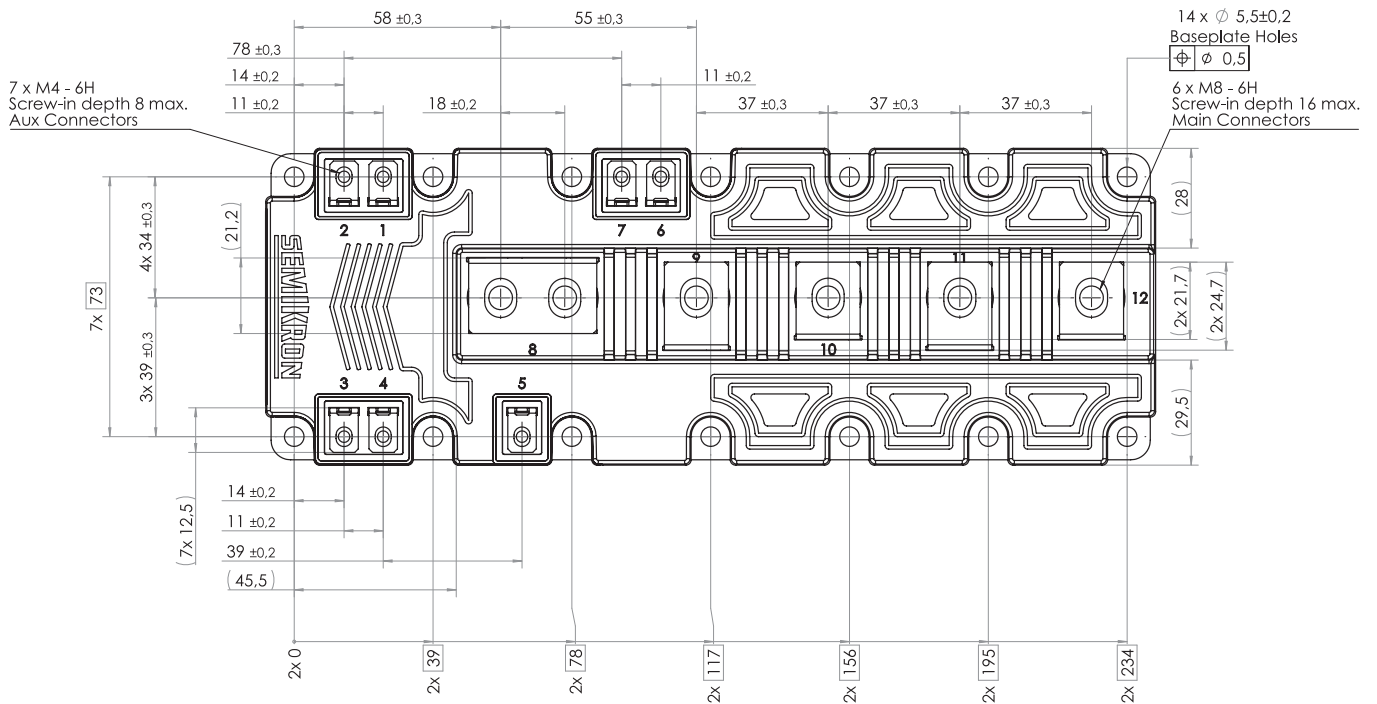
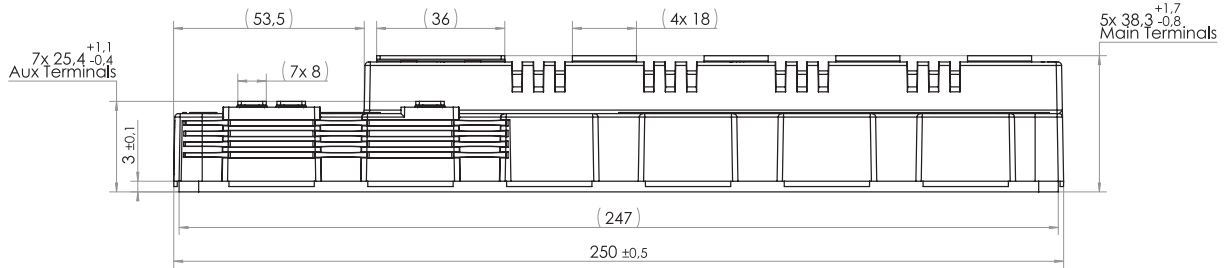
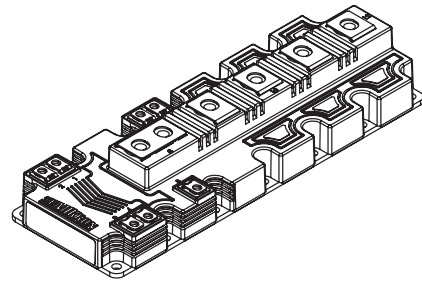
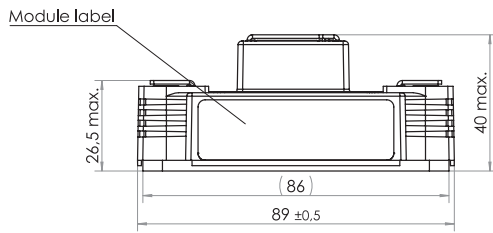


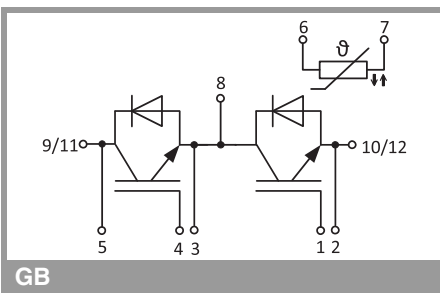
Fig. 14: Typ. gate charge characteristic

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- Dimensions in mm
- General tolerances ±0.5mm

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

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